

MCR22 SERIES

SILICON CONTROLLED RECTIFIERS

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.
- 150 A for 2 μs Safe Area

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive off-state voltage(1)			
$(R_{GK} = 1K, T_J = -40 \text{ to } +110^{\circ}C, \text{ sine wave, } 50 \text{ to } 60\text{Hz})$			
MCR22-2		50	
MCR22-3	VDRM	100	
MCR22-4	V	200	V
MCR22-5	V RRM	300	
MCR22-6		400	
MCR22-7		500	
MCR22-8		600	
On-state RMS current (180° conduction angles, $T_C = 80$ °C)	I _{T(RMS)}	1.5	Α
Peak non-repetitive surge current			^
(half-cycle, sine wave, 60Hz, $T_A = 25^{\circ}C$)	Ітѕм	15	A
Circuit fusing consideration (t = 8.3ms)	I²t	0.9	A ² s
Forward peak gate power (pulse width $\leq 1.0 \mu s$, $T_A = 25 ^{\circ}C$)	Р _{БМ}	0.5	W
Forward average gate power (t = 8.3ms, T _A = 25°C)	P _{G(AV)}	0.1	W
Forward peak gate current (pulse width ≤ 1.0µs, T _A = 25°C)	I _{GM}	0.2	Α
Reverse peak gate voltage (pulse width ≤ 1.0μs, T _A = 25°C)	V _{RGM}	5.0	V
Operating temperature range @ rated V _{RRM} and V _{DRM}	Tı	-40 to +110	°C
Storage temperature range	T _{stg}	-40 to +150	°C

Note 1: Vorus and Variety of all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

THERMAL CHARACTERISTICS

THERWIAL CHARACTERISTICS				
Characteristic	Symbol	Maximum	Unit	
Thermal resistance, junction to case	R _{eJC}	50	°C/W	
Thermal resistance, junction to ambient	R _{ΘJA}	160	°C/W	
Lead solder temperature (lead length ≥ 1/16" from case, 10s max)	TL	260	°C	

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Peak forward or reverse blocking current (V _{AK} = Rated V _{DRM} or V _{RRM} , R _{GK} = 1000 Ω) T_C = 25°C T_C = 110°C	I _{DRM} , I _{RRM}			10 200	μА
ON CHARACTERISTICS					
Peak forward on-state voltage* (I _{TM} = 1A)	V _{TM}	-	1.2	1.7	٧



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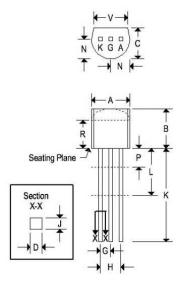
Gate trigger current (continuous dc) $^{(2)}$ ($V_{AK} = 6V$, $R_L = 100\Omega$)					
T _C = 25°C	l _{GT}	-	30	200	μΑ
$T_C = -40$ °C		-	-	500	
Gate trigger voltage (continuous dc) (2)					
$(V_{AK} = 7V, R_L = 100\Omega)$	V				V
$T_C = 25^{\circ}C$	V_{GT}	-	-	0.8	V
$T_C = -40$ °C		-	-	1.2	
Gate non-trigger voltage*	V_{GD}				V
$(V_{AK} = 12V, R_L = 100\Omega, T_C = 110^{\circ}C)$		0.1	-	-	
Holding current	I _H				mA
(V _{AK} = 12V, gate open, initiating current = 200mA)					
$T_C = 25^{\circ}C$		-	2.0	5.0	
$T_C = -40^{\circ}C$		-	-	10	
DYNAMIC CHARACTERISTICS					
Critical rate of rise of off-state voltage (T _C = 110°C)	dv/dt	-	25	-	V/µs
* Dula quidth < 1 Ones dutu qual < 19/			•		

^{*} Pulse width \leq 1.0ms, duty cycle \leq 1%.

Note 2: R_{GK} current not included in measurement.

MECHANICAL CHARACTERISTICS

Case:	TO-92
Marking:	Body painted, alpha-numeric
Pin out:	See below



	TO-92					
	Inches		Millim	lillimeters		
	Min	Max	Min	Max		
Α	0.175	0.205	4.450	5.200		
В	0.170	0.210	4.320	5.330		
С	0.125	0.165	3.180	4.190		
D	0.016	0.022	0.410	0.550		
F	0.016	0.019	0.410	0.480		
G	0.045	0.055	1.150	1.390		
Н	0.095	0.105	2.420	2.660		
J	0.015	0.020	0.390	0.500		
K	0.500	-	12.700			
L	0.250	186	6.350			
N	0.080	0.105	2.040	2.660		
Р	2	0.100	- 1	2.540		
R	0.115	199	2.930	199		
٧	0.135	1925	3.430	723		



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CURRENT DERATING

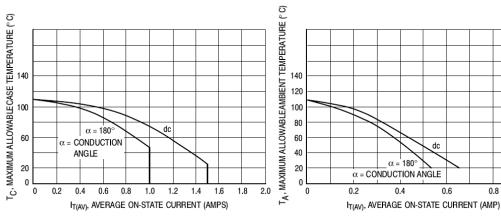


Figure 1. Maximum Case Temperature

Figure 2. Maximum Ambient Temperature

1.0

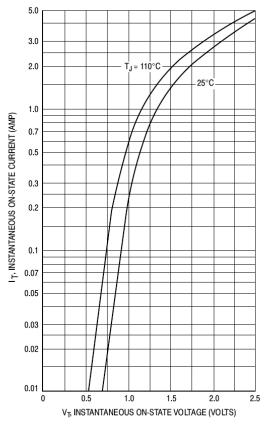


Figure 3. Typical Forward Voltage



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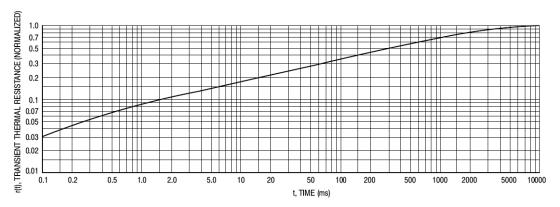


Figure 4. Thermal Response

TYPICAL CHARACTERISTICS

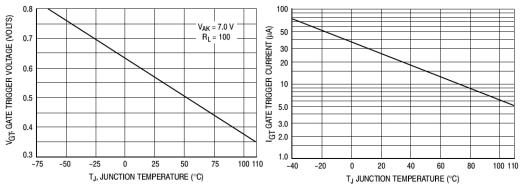


Figure 5. Typical Gate Trigger Voltage

Figure 6. Typical Gate Trigger Current

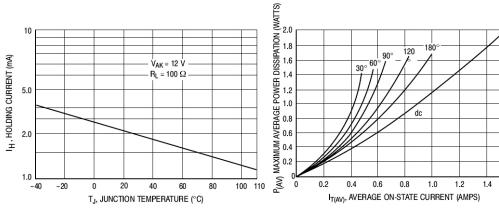


Figure 7. Typical Holding Current

Figure 8. Power Dissipation